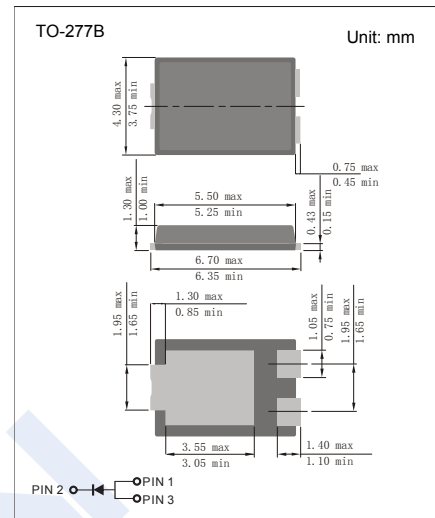


## Schottky Diodes

### KBR15L60SP5

#### ■ Features

- Low Forward Voltage Drop
- Excellent High Temperature Stability
- Trench Schottky Design using 8" Advanced Technology
- Lead Free Finish, RoHS Compliant
- Excellent ESD protection up to 30KV.



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	VRRM	60	V
Working Peak Reverse Voltage	VRWM	60	
DC Blocking Voltage	VR	60	
Average Forward Rectified Current	IFAV	15	A
Peak Forward Surge Current @ 60Hz	IFSM	300	
Thermal Resistance Junction to Case	R <sub>θJC</sub>	13	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature range	Tstg	-65 to 150	

#### ■ Electrical Characteristics Ta = 25°C

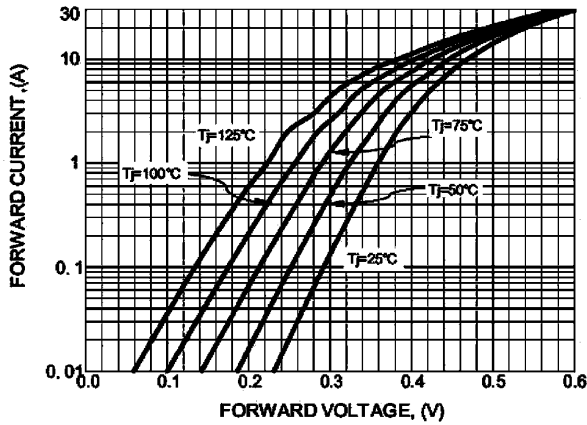
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	VR	IR= 0.5 mA	60			V
Forward voltage	VF1	IF= 3 A, TJ=25°C			0.5	
	VF2	IF= 3 A, TJ=125°C		0.28		
	VF3	IF= 15 A, TJ=25°C			0.54	
	VF4	IF= 15 A, TJ=125°C		0.44		
Reverse voltage leakage current	IR1	VR= 60 V, TJ=25°C			50	uA
	IR2	VR= 60 V, TJ=125°C		12		mA

# Schottky Diodes

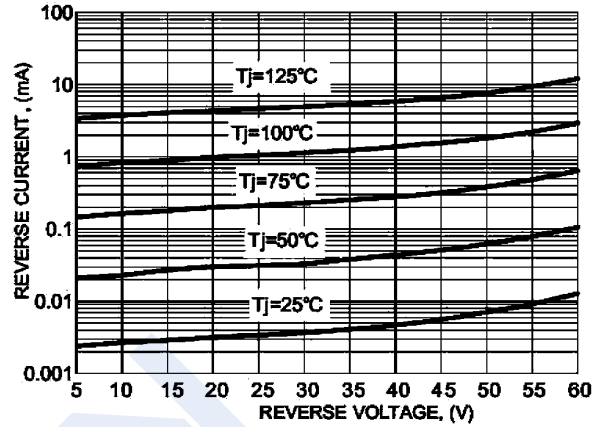
## KBR15L60SP5

■ Typical Characteristics

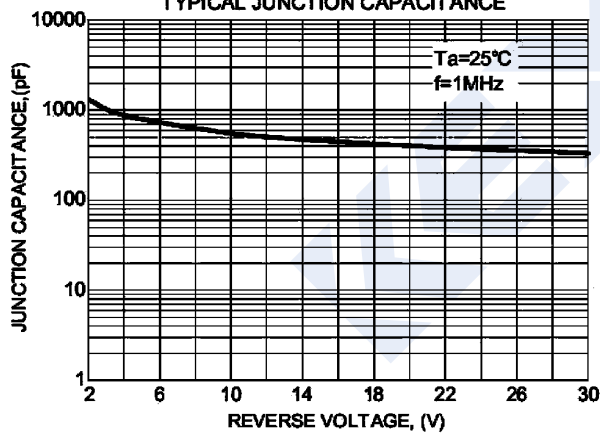
TYPICAL FORWARD CHARACTERISTICS



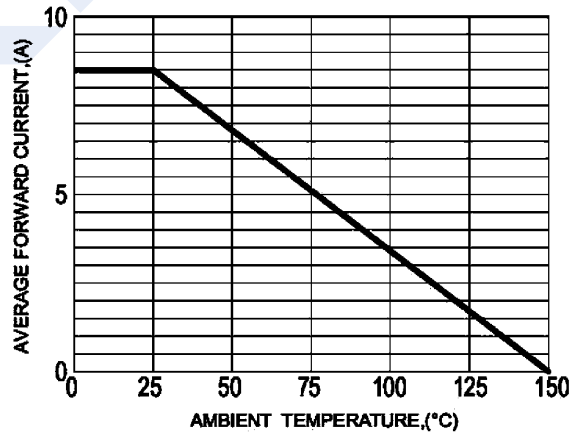
TYPICAL REVERSE LEAKAGE CHARACTERISTICS



TYPICAL JUNCTION CAPACITANCE



TYPICAL FORWARD CURRENT DERATING CURVE



MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

